

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
1	BRS	L1	0	wuwen adj1 yi.in.	USPA T; US-P GPUB ;	EPO; 2003/02/1 JPO; 1 17:18 DERW ENT; IBM TDB	
2	BRS	L2	0	diana adj1 morales.in.	USPA T; US-P GPUB ;	EPO; 2003/02/1 JPO; 1 17:18 DERW ENT; IBM TDB	
3	BRS	L3	16	chi adj1 wu.in.	USPA T; US-P GPUB ;	EPO; 2003/02/1 JPO; 1 17:18 DERW ENT; IBM TDB	
4	BRS	L4	3	'3 and physical near vapor	USPA T; US-P GPUB ;	EPO; 2003/02/1 JPO; 1 17:19 DERW ENT; IBM TDB	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
5	BRS	L5	0	ritesh adj1 shah.in.	USPA T; US-P GPUB ;	2003/02/1 1 17:20	
6	BRS	L6	0	jeff adj1 keller.in.	USPA T; US-P GPUB ;	2003/02/1 1 17:20	
7	BRS	L7	1856	438/612.cccls.	USPA T; US-P GPUB ;	2003/02/1 1 17:20	
8	BRS	L8	22	7 and (physical nearl vapor)	USPA T; US-P GPUB ;	2003/02/1 1 17:25	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
9	BRS	L9	11971	physical near vapor near deposition	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2003/02/1 1 17:59	
10	BRS	L11	1	(physical near vapor near deposition) near10 (non-magnetic) near8 (silicon)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2003/02/1 1 17:27	
11	BRS	L10	43	(physical near vapor near deposition) near10 (non-magnetic)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2003/02/1 1 17:38	
12	BRS	L12	177	(PVD) near10 magnetic	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2003/02/1 1 17:36	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
13	BRS	L13	1	(PVD) near10 magnetic near10 phase	USPA; T; US-P; GPUB; ; EPO; JPO; DERW; ENT; IBM; TDB	2003/02/1 1 17:36	
14	BRS	L14	219	(physical near vapor near deposition) near10 (magnetic)	USPA; T; US-P; GPUB; ; EPO; JPO; DERW; ENT; IBM; TDB	2003/02/1 1 17:38	
15	BRS	L15	4	(physical near vapor near deposition) near10 (magnetic) near10 (phase)	USPA; T; US-P; GPUB; ; EPO; JPO; DERW; ENT; IBM; TDB	2003/02/1 1 17:40	
16	BRS	L16	36	(vapor near deposition) near10 (magnetic) near10 (phase)	USPA; T; US-P; GPUB; ; EPO; JPO; DERW; ENT; IBM; TDB	2003/02/1 1 17:40	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
17	BRS	L17	2	(vapor near deposition) near10 (magnetic) near10 (phase) near10 (silicon)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2003/02/1 1 17:42	
18	BRS	L18	264	(vapor near deposition) near10 (phase) near10 (silicon)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2003/02/1 1 17:42	
19	BRS	L19	2	(vapor near deposition) near10 (one near phase) near10 (silicon)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2003/02/1 1 17:44	
20	BRS	L20	6	(vapor near deposition) near10 (one near phase)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2003/02/1 1 17:50	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
21	BRS	L21	88901	(film) near10 deposition	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2003/02/1 1 17:50	
22	BRS	L22	25835	(thin near film) near10 deposition	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2003/02/1 1 17:51	
23	BRS	L23	0	(thin near film) near10 deposition near10 (one near phase)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2003/02/1 1 17:52	
24	BRS	L24	1	(thin near film) near10 deposition near20 (one near phase)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2003/02/1 1 17:53	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
25	BRS	L25	916	(thin near film) near10 deposition near20 (phase)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2003/02/1 1 17:53	
26	BRS	L26	433	(thin near film) near10 vapor near deposition near20 (phase)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2003/02/1 1 17:54	
27	BRS	L27	1	69654 (thin near film) near10 vapor near deposition near20 (phase) nera5 silicon	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2003/02/1 1 17:54	
28	BRS	L29	0	(magnetic) near5 (thin near film) near10 vapor near deposition near20 (phase) near silicon	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2003/02/1 1 17:55	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
29	BRS	L28	16	(thin near film) near10 vapor near deposition near20 (phase) near silicon	USPA T; US-P GPUB ; EPO; 2003/02/1 JPO; 1 17:57 DERW ENT; IBM TDB		
30	BRS	L30	81	(film) near10 vapor near deposition near20 (phase) near silicon	USPA T; US-P GPUB ; EPO; 2003/02/1 JPO; 1 17:58 DERW ENT; IBM TDB		
31	BRS	L31	1	(magnetic near10 film) near10 vapor near deposition near20 (phase) near silicon	USPA T; US-P GPUB ; EPO; 2003/02/1 JPO; 1 17:59 DERW ENT; IBM TDB		
32	BRS	L32	228	physical near vapor near deposition near3 target	USPA T; US-P GPUB ; EPO; 2003/02/1 JPO; 1 18:00 DERW ENT; IBM TDB		

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
33	BRS	L33	10	magnetic near8 physical near vapor near deposition near3 target	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2003/02/1 1 18:04	
34	BRS	L35	0	silicon near8 physical near vapor near deposition near3 target near phase	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2003/02/1 1 18:04	
35	BRS	L36	5	phase near8 physical near vapor near deposition near3 target	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2003/02/1 1 18:05	
36	BRS	L34	25	silicon near8 physical near vapor near deposition near3 target	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2003/02/1 1 18:11	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
37	BRS	L37	440	silicon near8 physical near vapor near deposition	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2003/02/1 1 18:11	
38	BRS	L38	2	silicon near8 physical near vapor near deposition near8 phase	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2003/02/1 1 18:12	
39	BRS	L39	245	physical near vapor near deposition near8 phase	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2003/02/1 1 18:12	
40	BRS	L40	3	magnetic near8 physical near vapor near deposition near8 phase	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2003/02/1 1 18:14	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
41	BRS	L41	13450 4	438/\$.ccls.	USPA T; US-P GPUB ;	2003/02/1 1 18:15	
42	BRS	L42	11980	41 and (physical near vapor) or (PVD)	USPA T; US-P GPUB ;	2003/02/1 1 18:15	
43	BRS	L43	11168	41 and target near8 (physical near vapor) or (PVD)	USPA T; US-P GPUB ;	2003/02/1 1 18:16	
44	BRS	L44	270	41 and target near8 (physical near vapor) or (PVD) near8 magnetic	USPA T; US-P GPUB ;	2003/02/1 1 18:16	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
45	BRS	L45	158	44 and silicon	USPA T; US-P GPUB ;	EPO; 2003/02/1 JPO; 1 18:16 DERW ENT; IBM TDB	
46	BRS	L46	64	45 and phase	USPA T; US-P GPUB ;	EPO; 2003/02/1 JPO; 1 18:16 DERW ENT; IBM TDB	

	U	1	Document ID	Title	Current OR	Pages	Issue Date
1			US 20030022477 A1	Formation of electroplate solder on an organic circuit board for flip chip joints and board to board solder joints	438/612	16	20030130
2			US 20030013290 A1	Semiconductor device and method of formation	438/612	10	20030116
3			US 20010053567 A1	Method of forming a test insert for interfacing a device containing contact bumps with a test substrate	438/127	25	20011220
4			US 20010016408 A1	Mask repattern process	438/618	11	20010823
5			US 6472304 B2	Wire bonding to copper	438/612	12	20021029
6			US 6461954 B1	Method and an apparatus for forming an under bump metallization structure	438/613	7	20021008
7			US 6451681 B1	Method of forming copper interconnection utilizing aluminum capping film	438/601	11	20020917
8			US 6448171 B1	Microelectronic fabrication having formed therein terminal electrode structure providing enhanced passivation and enhanced bondability	438/614	9	20020910
9			US 6420254 B1	Recessed bond pad	438/612	22	20020716
10			US 6395626 B1	Method of forming bonding projecting electrodes	438/613	16	20020528

	U	1	Document ID	Title	Current OR	Pages	Issue Date
11	<input type="checkbox"/>	<input type="checkbox"/>	US 6376353 B1	Aluminum and copper bimetallic bond pad scheme for copper damascene interconnects	438/612	18	20020423
12	<input type="checkbox"/>	<input type="checkbox"/>	US 6362087 B1	Method for fabricating a microelectronic fabrication having formed therein a redistribution structure	438/597	9	20020326
13	<input type="checkbox"/>	<input type="checkbox"/>	US 6358832 B1	Method of forming barrier layers for damascene interconnects	438/612	13	20020319
14	<input type="checkbox"/>	<input type="checkbox"/>	US 6300234 B1	Process for forming an electrical device	438/612	10	20011009
15	<input type="checkbox"/>	<input type="checkbox"/>	US 6297140 B1	Method to plate C4 to copper stud	438/612	9	20011002
16	<input type="checkbox"/>	<input type="checkbox"/>	US 6281041 B1	Process to make a tall solder ball by placing a eutectic solder ball on top of a high lead solder ball	438/106	10	20010828
17	<input type="checkbox"/>	<input type="checkbox"/>	US 6245655 B1	Method for planarized deposition of a material	438/612	14	20010612
18	<input type="checkbox"/>	<input type="checkbox"/>	US 6228687 B1	Wafer-level package and methods of fabricating	438/125	16	20010508

	U	1	Document ID	Title	Current OR Pages	Pages	Issue Date
19	<input type="checkbox"/>	<input type="checkbox"/>	US 6214716 B1	Semiconductor substrate-based BGA interconnection and methods of fabrication same	438/612	17	20010410
20	<input type="checkbox"/>	<input type="checkbox"/>	US 6198170 B1	Bonding pad and support structure and method for their fabrication	257/784	24	20010306
21	<input type="checkbox"/>	<input type="checkbox"/>	US 6169021 B1	Method of making a metallized recess in a substrate	438/612	17	20010102
22	<input type="checkbox"/>	<input type="checkbox"/>	US 6110823 A	Method of modifying the thickness of a plating on a member by creating a temperature gradient on the member, applications for employing such a method, and structures resulting from such a method	438/660	130	20000829